

subjecting said semiconductor film to oxygen plasma; and  
crystallizing said initial semiconductor film to obtain a crystalline semiconductor  
film.

46. A method according to claim 45, wherein said crystallizing is performed by  
irradiating with an infrared ray or a laser light.

47. A method according to claim 45, wherein said initial semiconductor film is  
crystallized without melting through a solid state.

48. A method according to claim 45, wherein an oxide film of said semiconductor  
film is formed thereon by said oxygen plasma.

49. A method for manufacturing a semiconductor device comprising steps of:  
forming an initial semiconductor film formed over a substrate;  
subjecting said semiconductor film to oxygen plasma; and  
irradiating said semiconductor film with an infrared ray or a laser light.

50. A method according to claim 49, wherein said initial semiconductor film is  
crystallized without melting through a solid state.

51. A method according to claim 49, wherein an oxide film of said semiconductor  
film is formed thereon by said oxygen plasma.

52. A method for manufacturing a semiconductor device comprising steps of:  
contacting a material for promoting crystallization to at least a part of an initial  
semiconductor film formed over a substrate;  
subjecting said semiconductor film to oxygen plasma; and

53. A method according to claim 52, wherein said crystallizing is performed by irradiating with an infrared ray or a laser light.

54. A method according to claim 52, wherein said initial semiconductor film is crystallized without melting through a solid state.

55. A method according to claim 52, wherein an oxide film of said semiconductor film is formed thereon by said oxygen plasma.

56. A method for manufacturing a semiconductor device comprising steps of:  
contacting a material for promoting crystallization to at least a part of an initial semiconductor film formed over a substrate;  
subjecting said semiconductor film to oxygen plasma;  
crystallizing said initial semiconductor film using said material, to obtain a crystalline semiconductor film; and  
patterning said crystalline semiconductor film.

57. A method according to claim 56, wherein said crystallizing is performed by irradiating with an infrared ray or a laser light.

58. A method according to claim 56, wherein said initial semiconductor film is crystallized without melting through a solid state.

59. A method according to claim 56, wherein an oxide film of said semiconductor film is formed thereon by said oxygen plasma. -1